

GTM CORPORATION

ISSUED DATE :2004/06/09
REVISED DATE :2004/11/29B

G2N5401

PNP EPITAXIAL PLANAR TANSISTOR

Description

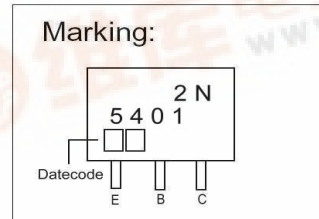
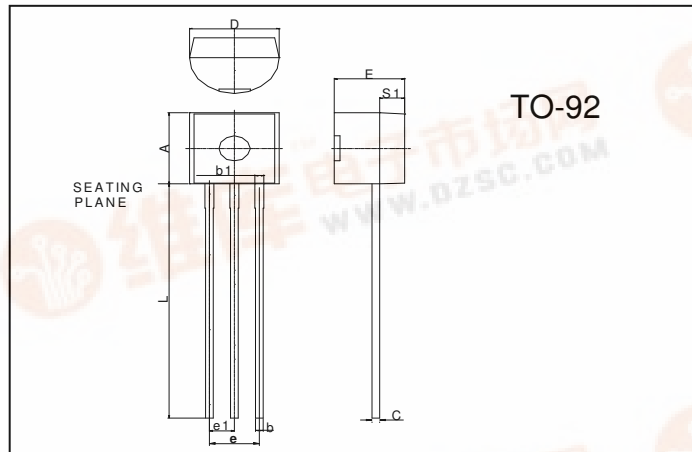
The G2N5401 is designed for general purpose applications requiring high breakdown voltages.

Features

*Complementary to NPN Type G2N5551

*High Collector-Emitter Breakdown Voltage ($V_{CEO}=150V@I_C=1mA$)

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ C$
Collector to Base Voltage	V_{CBO}	-160	V
Collector to Emitter Voltage	V_{CEO}	-150	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Total Power Dissipation	P_D	625	mW

Characteristics at $T_a = 25^\circ C$

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-160	-	-	V	$I_C=-100\mu A, I_E=0$
BV_{CEO}	-150	-	-	V	$I_C=-1mA, I_B=0$
BV_{EBO}	-5	-	-	V	$I_E=-10\mu A, I_C=0$
I_{CBO}	-	-	-50	nA	$V_{CB}=-120V, I_E=0$
I_{EBO}	-	-	-50	nA	$V_{EB}=-3V, I_C=0$
$*V_{CE(sat)1}$	-	-	-0.2	V	$I_C=-10mA, I_B=-1mA$
$*V_{CE(sat)2}$	-	-	-0.5	mV	$I_C=-50mA, I_B=-5mA$
$*V_{BE(sat)1}$	-	-	-1	V	$I_C=-10mA, I_B=-1mA$
$*V_{BE(sat)2}$	-	-	-1	V	$I_C=-50mA, I_B=-5mA$
$*h_{FE1}$	50	-	-		$V_{CE}=-5V, I_B=-1mA$
$*h_{FE2}$	80	160	400		$V_{CE}=-5V, I_C=-10mA$
$*h_{FE3}$	50	-	-		$V_{CE}=-5V, I_C=-50mA$
f_T	100	-	300	MHz	$V_{CE}=-10V, I_C=-10mA, f=100MHz$
C_{ob}	-	-	6	pF	$V_{CB}=-10V, f=1MHz, I_E=0$

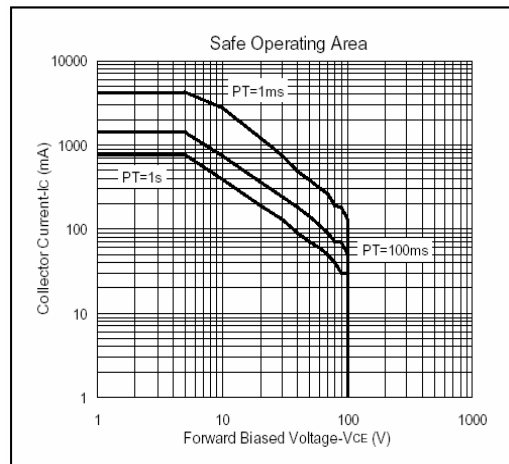
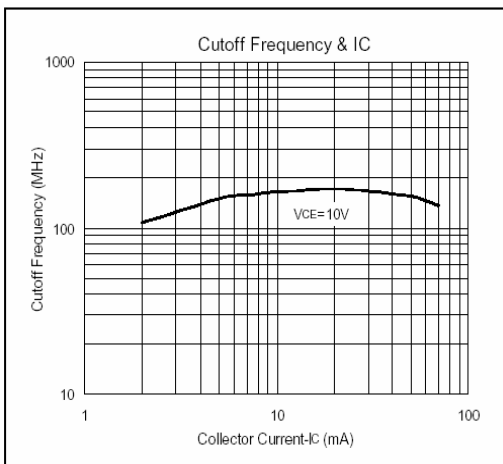
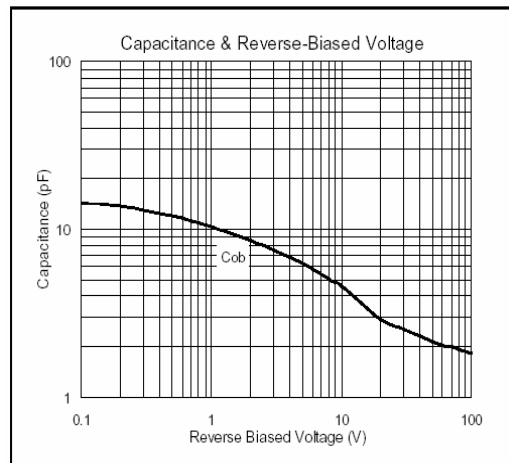
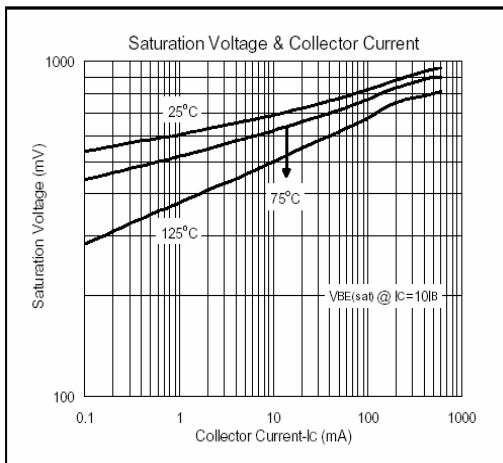
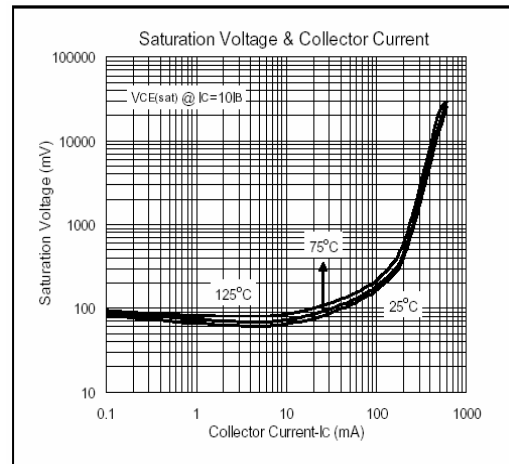
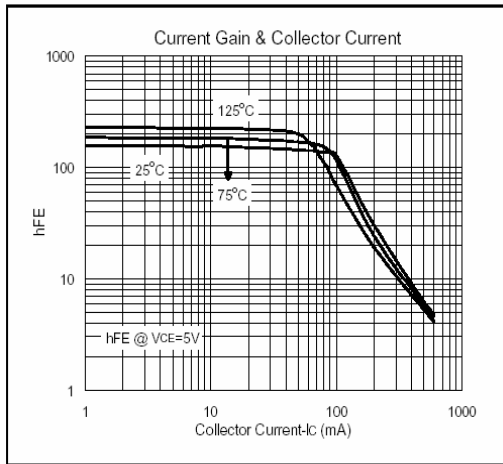
* Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

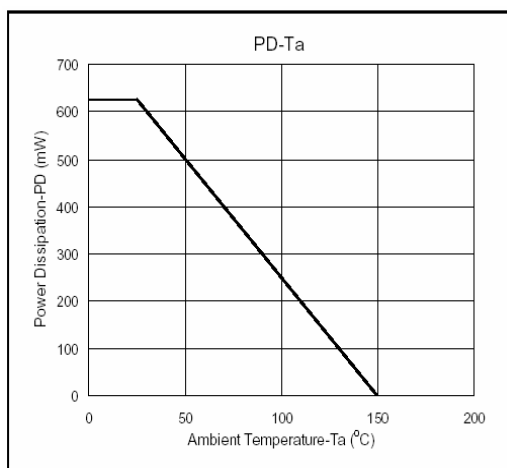
Classification Of h_{FE2}

Rank	A	N	C
Range	80-200	100-240	160-400



Characteristics Curve





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